

#### ABSTRACT OF THE DISCLOSURE

An improved method of rewriting data in a memory is provided. A flash memory has a sector partitioned into a plurality of areas. In the flash memory, data are written to  
5 a same position in the respective areas. When writing rewrite data, an exclusive-OR of the rewrite data and data at a target position in a first area is taken, and an exclusive-OR of the exclusive-OR data and data at the same position in a second area is taken. Similar steps are repeated in sequence for the rest  
10 of the areas. In the course of repeating these steps, when data at the target position of the area concerned are an initial value, then the most recent exclusive-OR data are written to the position in that area.